

ISSCC'02 Feb. 5 Evening Panel

# Low-Voltage Design or the End of CMOS Scaling?

**Organizer:** Akira Matsuzawa (Matsushita)  
Kunihiro Iizuka (Sharp)

**Moderator:** Takayasu Sakurai (Univ. of Tokyo)

## Panelists:

|                           |                      |                                  |
|---------------------------|----------------------|----------------------------------|
| <b>Asad Abidi</b>         | <b>U.C.L.A</b>       | <b>Analog/RF</b>                 |
| <b>Daniel Senderowicz</b> | <b>SynchroDesign</b> | <b>Analog/SW cap.</b>            |
| <b>Akira Matsuzawa</b>    | <b>Matsushita</b>    | <b>Analog/DAC, DAC</b>           |
| <b>Alex Shubat</b>        | <b>Virage Logic</b>  | <b>Memory/SRAM</b>               |
| <b>Junichi Miyamoto</b>   | <b>Toshiba</b>       | <b>Memory/Non-vol.</b>           |
| <b>Shekhar Borker</b>     | <b>Intel</b>         | <b>Digital/<math>\mu</math>P</b> |

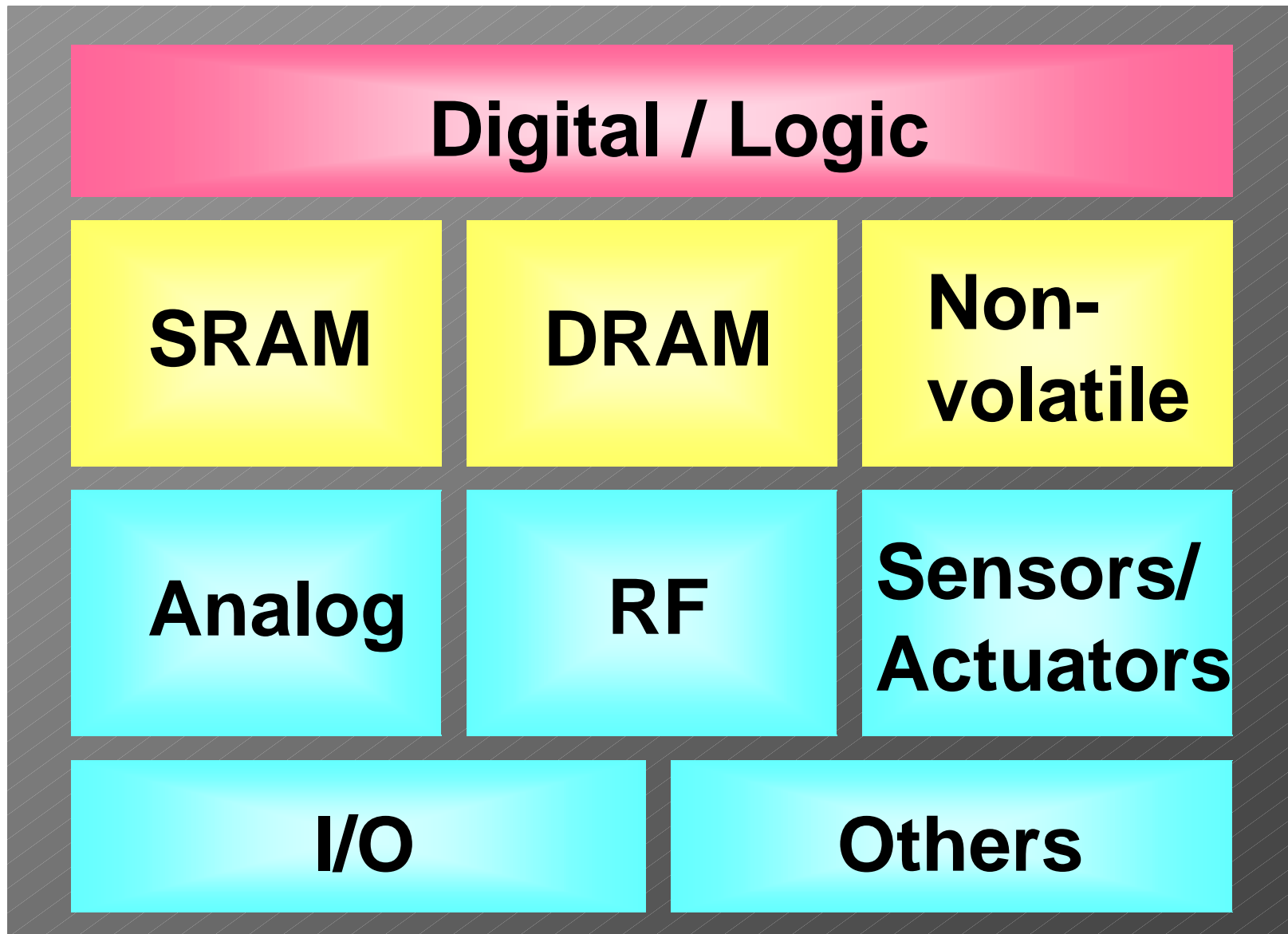
# Low-voltage design or the end of CMOS scaling?

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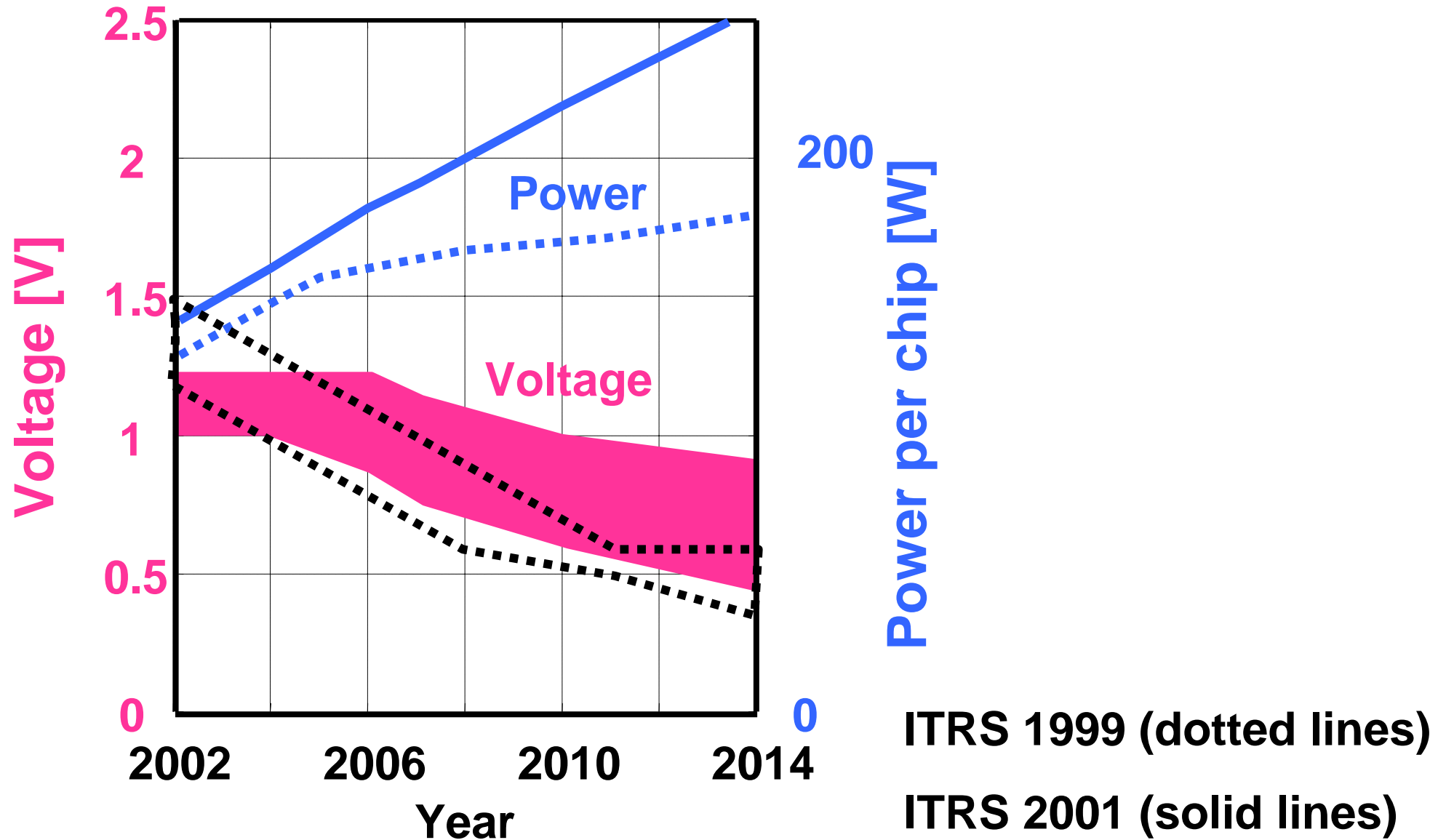
1. Is there minimum  $V_{DD}$ ? Why?
2. After the  $V_{DD,min}$  is reached, how can we improve the cost-performance w/o scaling?
3. What implications to the SoC design?

# System on a Chip (SoC) in 2010

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# V<sub>DD</sub> and power estimate from ITRS




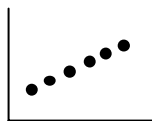
# How low can we go?

| Name      | Area    | VDD,min (V)   | Limitting factor                           |
|-----------|---------|---------------|--|
| Asad      | Analog  | 2.5~1V        | Dynamic range imposed by physical world    |
| Daniel    | Analog  | ~1.5V         | Dynamic Range, DEVICE LIMITATIONS          |
| Matsuzawa | Analog  | 0.8~1.8V      | Amplifior scheme→Headroom<br>Dynamic range |
| Alex      | Memory  | Will Scale    | $I_k/I_L$ , NM, Prpcess V                  |
| Miyamoto  | Memory  | follow logics | prpcess complexity                         |
| Shekhar   | Digital | <200mv        | Micro-Architectures to comprehend effect   |

# How to improve cost-perf. w/o scaling

| Name      | Area    | Mainly Technology or Circuit?           | Possible cost-perf. improvement senario   |
|-----------|---------|---|---|
| Asad      | Analog  | Both                                    | Better, more compact passives   |
| Daniel    | Analog  | Both                                    | Operate at the highest possible VDD and enjoy the high-performance devices with clever design techniques.                                 |
| Matsuzawa | Analog  | Technology and CKT                      | <ul style="list-style-type: none"> <li>• FD-SOI for switch</li> <li>• Hi-accurale passive</li> <li>• Small analog, big digital</li> </ul> |
| Alex      | Memory  | Both T(1/3)<br>C(3/3)                   | <ul style="list-style-type: none"> <li>• Optimization at small block Lennel</li> <li>• More options T+C</li> </ul>                        |
| Miyamoto  | Memory  | Both                                    | miniaturization-(Muliti-bit)-Newmaterial<br>-stack(3D)  |
| Shekhar   | Digital | Both. Technology&c<br>ircuit to support | Tech.will provide integration capatit,<br>circuib will exploib it to obtain higher<br>performance   |

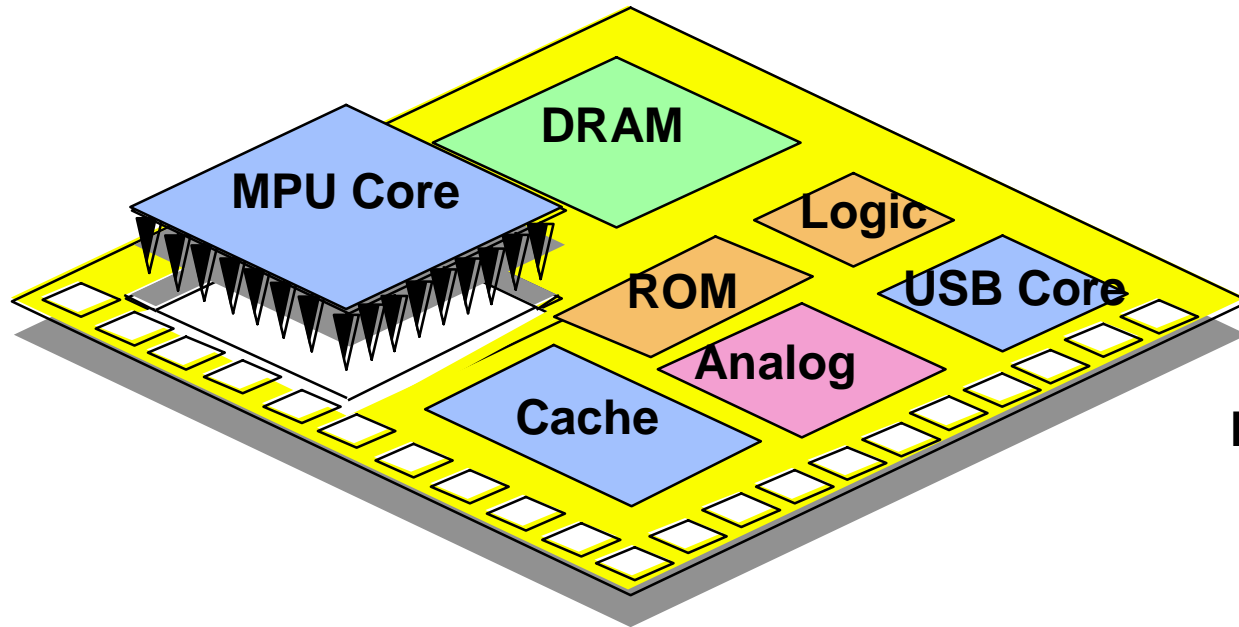
# Implications to SoC in 2010

| Name      | Area    | # of VDD's  | # of tr. Option   | Vary VDD in time? | Vary VTH in time?      | SoC/SiP MOC                |
|-----------|---------|---|---|-------------------|------------------------|----------------------------|
| Asad      | Analog  | 2   | 4   | No                | No                     | MOC                        |
| Daniel    | Analog  | 2   | 4   | No                | No                     | NO                         |
| Matsuzawa | Analog  | 3   | 5   | YES               | YES                    | 50%SoC<br>50%SiP           |
| Alex      | Memory  |  |  | YES               | Yes<br>(BACK B, Reast) | Soc=#                      |
| Miyamoto  | Memory  | 2(1 for I/O<br>1 for V <sub>DD</sub> )  | at least<br>4   | No                | YES                    | depending on<br>the system |
| Shekhar   | Digital | >3  | 2-3<br>2-Digital  | YES               | YES                    | NO                         |

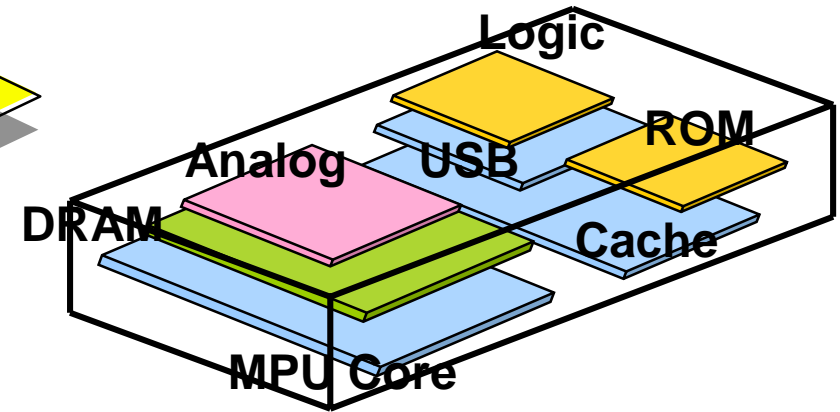
Basic PMOS-high Thick.tox

Basic NMOS high Thick.tox

# No SoC, please



**System on a Chip**



**System in a Package**

- Voltage optimized process for each die (Analog, DRAM, MEMS...)
- Good voltage isolation